TOSHIBA PHOTOCOUPLER GaAIAs IRED + PHOTO-IC

Preliminary

TLP719

DIGITAL LOGIC GROUND ISOLATION.

LINE RECEIVER.

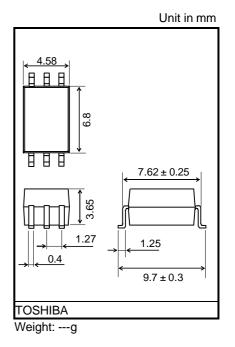
MICROPROCESSOR SYSTEM INTERFACES.
SWITCHING POWER SUPPLY FEEDBACK CONTROL.
TRANSISTOR INVERTOR.

The TOSHIBA TLP719 consists of a GaAlAs high-output light emitting diode and a high speed detector.

This unit is 6-lead SDIP. TLP719 is 50% smaller than 8PIN DIP and has suited the safety standard reinforced insulation class. So mounting area in safety standard required equipment can be reduced.

TLP719 has a Faraday shield integrated on the photodetector chip provides an effective common mode noise transient immunity.

So this is suitable for application in noisy environmental condition.



Open Collector

Package Type : SDIP6

• Isolation voltage : 5000 Vrms (Min.)

• Common mode Transient Immunity

: ±10kV/us(Min.) @VCM=400V

• Switching speed : t_{pHL} = 0.8µs , t_{pLH} = 0.8µs (Max.)

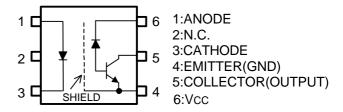
@ $I_F = 16mA$, $V_{CC} = 5V$,

 $R_L = 1.9kO$, Ta = 25°C

- TTL Compatible
- · Construction Mechanical Rating

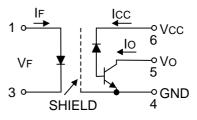
| | 7.62 mm pich standard type | 10.16 mm pich TLPXXXF type |
|----------------------|----------------------------|-------------------------------|
| Creepage Distance | 7.0 mm (Min) | 8.0 mm (Min) |
| Clearance | 7.0 mm (Min) | 8.0 mm (Min) |
| Insulation Thickness | 0.4 mm (Min) | 0.4 mm (Min) |

PIN CONFIGURATION (Top view)



SCHEMATIC

1



A 0.1µF bypass capacitor must be connected between pins 4 and 6.

Maximum Ratings (Ta = 25°C)

| | Characteristic | | Symbol | Rating | Unit |
|---------------------------|--------------------------------------|----------|------------------|---------|------|
| | Forward current | (Note 1) | lF | 25 | mA |
| | Pulse forward current | (Note 2) | IFP | 50 | mA |
| LED | Peak transient forward current | (Note 3) | I _{FPT} | 1 | А |
| ۳ | Reverse voltage | | V _R | 5 | V |
| | Diode power dissipation | (Note 4) | P _D | 45 | mW |
| | Junction Temperature | | Tj | 125 | °C |
| ctor | Output current | | IO | 8 | mA |
| | Peak output current | | I _{OP} | 16 | mA |
| | Output voltage | | Vo | -0.5~20 | V |
| Detector | Supply voltage | | V _{CC} | -0.5~30 | V |
| | Output power dissipation | (Note 5) | Po | 100 | mW |
| | Junction Temperature | | Tj | 125 | °C |
| Оре | Operating temperature range | | T _{opr} | -55~100 | °C |
| Storage temperature range | | | T _{opr} | -55~125 | °C |
| Lea | d solder temperature (10s) | | T _{sol} | 260 | °C |
| Isol (AC | ation voltage , 1min., R.H.= 60%) | (Note 6) | BVS | 5000 | Vrms |

(Note 1) Derate 0.45mA / °C above 70°C.

(Note 2) 50% duty cycle, 1ms pulse width. Derate 0.9mA / °C above 70°C.

(Note 3) Pulse width = 1μ s, 300pps.

(Note 4) Derate 0.8mW / °C above 70°C.

(Note 5) Derate 1.8mW / °C above 70°C.

(Note 6) Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4, 5 and 6 shorted together.

Electrical Characteristics (Ta = 25°C)

| | Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|------------|---|----------------------|---|------|------|------|---------|
| | Forward voltage | V _F | I _F = 16mA | | 1.65 | 1.85 | V |
| ۵ | Forward voltage Temperature coefficient | ?V _F /?Ta | I _F = 16mA | ? | -2 | ? | mV / °C |
| Ē | Reverse current | I _R | V _R = 5V | ? | ? | 10 | μΑ |
| | Capacitance between terminal | C _T | V _F = 0V , f = 1MHz | ? | 45 | ? | pF |
| | | I _{OH (1)} | $I_F = 0mA$, $V_{CC} = V_O = 5.5V$ | ? | 3 | 500 | nA |
| High level | High level output current | I _{OH} (2) | I _F = 0mA ,V _{CC} = 30V V _O = 20V | ? | ? | 5 | μΑ |
| | | ГОН | I _F = 0mA ,V _{CC} = 30V V _O = 20V,Ta = 70°C | ? | ? | 50 | μΛ |
| De | High level supply voltage | Іссн | I _F = 0mA ,V _{CC} = 30V | ? | 0.01 | 1 | μΑ |
| | Supply voltage | Vcc | I _{CC} = 0.01mA | 30 | ? | ? | V |
| | Output voltage | Vo | I _O = 0.5mA | 20 | ? | ? | V |

Coupled Electrical Characteristics (Ta = 25°C)

| Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|--------------------------|---------------------------------|---|------|------|------|------|
| Current transfer ratio | I _O / I _F | $I_F = 16 \text{mA}$, $V_{CC} = 4.5 \text{V}$ $V_O = 0.4 \text{V}$ | 20 | ? | ? | % |
| Low level output voltage | V _{OL} | I _F = 16mA ,V _{CC} = 4.5V I _O = 2.4mA | ? | ? | 0.4 | V |

Isolation Characteristics (Ta = 25°C)

| Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|-----------------------------|--------|--|--------------------|------------------|------|------------------|
| Capacitance input to output | Cs | V = 0V, $f = 1MHz$ (Note 6) | ? | 0.8 | ? | pF |
| Isolation resistance | Rs | R.H. = 60% ,V _S = 500V (Note 6) | 1×10 ¹² | 10 ¹⁴ | ? | 0 |
| Isolation voltage | | AC,1 minute | 5000 | ? | ? | V |
| | | AC,1 second , in oil | ? | 10000 | ? | V _{rms} |
| | | DC,1 minute , in oil | ? | 10000 | ? | Vdc |

Switching Characteristics (Ta = 25°C, Vcc = 5V)

| Characteristic | | Symbol | Test Cir- cuit | Test Condition | Min. | Тур. | Max. | Unit |
|--|----------|------------------|----------------------|---|--------|------|------|--------|
| Propagation delay time (| (H? L) | t _{pHL} | Fig1 | I _F = 0? 16mA R _L = 1.9kO | ? | ? | 0.8 | μs |
| Propagation delay time (| (L? H) | t _{pLH} | | I _F = 16? 0mA R _L = 1.9kO | ? | ? | 0.8 | μs |
| Common mode transient immunity at logic high output (I | Note 7) | СМН | Fig2 | $I_F = 0 \text{mA}$, $V_{CM} = 400 V_{p-p}$ $R_L = 1.9 \text{kO}$ | 10000 | ? | ? | V/µs |
| Common mode transient immunity at logic low output | (Note 7) | CML | | $I_F = 16\text{mA}$, $V_{CM} = 400V_{p-p}$ $R_L = 1.9\text{kO}$ | -10000 | ? | ? | V / µs |

(Note 7) : CM_L is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state($V_O < 0.8V$). CM_H is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state($V_O > 2V$).

Fig 1.Switching Time Test Circuit

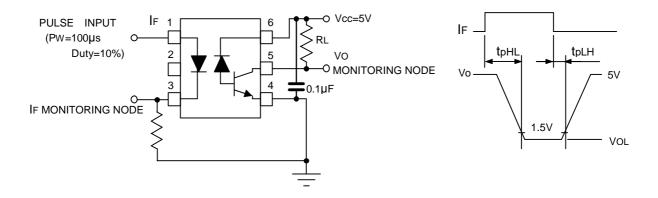
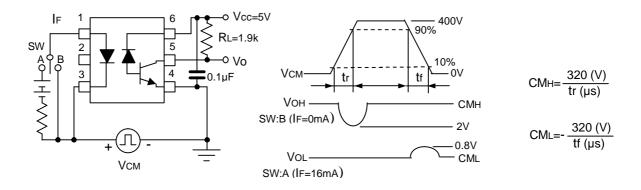


Fig 2.Common Mode Noise Immunity Test Circuit.



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